



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Yoshiki SAKUMA

Serial No.: 09/819,762

Filed: March 29, 2001

For: HETEROBIPOLAR TRANSISTOR AND A METHOD OF FORMING A SiGeC MIXED CRYSTAL LAYER

Examiner: Bradley W. Baumeister

Group Art Unit: 2815

AMENDMENT UNDER 37 C.F.R. §1.116
- EXPEDITED RESPONSE -
GROUP ART UNIT 2815

BOX AF

Commissioner for Patents
Washington, D. C. 20231

February 10, 2003

Sir:

In response to the Office Action dated October 9, 2002, please amend the application as follows and reconsider the application in view of the Remarks.

A Petition for a one month extension of time to file this response is being filed concurrently herewith.

IN THE CLAIMS

Please amend claims 1 and 11 and cancel claims 9 and 10 as follows.

1. (Amended) A heterobipolar transistor, comprising:

a substrate;

a collector layer of Si formed on said substrate;

a base layer formed on said collector layer; and

an emitter layer of Si formed on said base layer,

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